

TECHNICAL DATA DATA SHEET 171, REV. B Formerly Part Number SHD2263

HERMETIC POWER MOSFET - N-CHANNEL

FEATURES:

- 200 Volt, 0.21 Ohm, 14A MOSFET
- Isolated Hermetic Metal Package
- Fast Switching
- Low R_{DS (on)}
- Ceramic Seals available (Add a "C" to the part number, i.e. SHDC226403)
- Similar to IRFY240

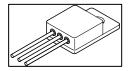
MAXIMUM RATINGS

ALL RATINGS ARE AT T_c = 25°C UNLESS OTHERWISE SPECIFIED.

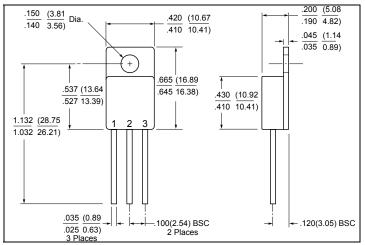
| RATING | SYMBOL | MIN. | TYP. | MAX. | UNITS |
|---|-----------------------------------|------|------|------|-------|
| GATE TO SOURCE VOLTAGE | V _{GS} | - | - | ±20 | Volts |
| ON-STATE DRAIN CURRENT $V_{DS} \ge 2V_{DS(on)}, V_{GS} = 10V$ | I _{D (on)} | - | - | 14 | Amps |
| PULSED DRAIN CURRENT $@ T_c = 25^{\circ}C$ | I _{DM} | - | - | ±56 | Amps |
| OPERATING AND STORAGE TEMPERATURE | T _{OP} /T _{STG} | -55 | - | +150 | °C |
| THERMAL RESISTANCE, JUNCTION TO CASE | $R_{	ext{	heta}JC}$ | - | - | 2.1 | °C/W |
| TOTAL DEVICE DISSIPATION @ T _C = 25°C | PD | - | - | 60 | Watts |

ELECTRICAL CHARACTERISTICS

| CHARACTERISTIC | | SYMBOL | MIN. | TYP. | MAX. | UNITS |
|--|---|------------------------|------|------|------|------------|
| DRAIN TO SOURCE BREAKDOWN VO | LTAGE | BV _{DSS} | 200 | - | - | Volts |
| V _{GS} | = 0V, I _D = 250 μA | | | | | |
| DRAIN TO SOURCE ON-STATE VOLTA | \GE | V _{DS(ON)} | - | 1.8 | 2.1 | Volts |
| | _s = 10V, I _D = 10A | | | | | |
| STATIC DRAIN TO SOURCE ON STATE | | | - | - | | |
| V_{GS} = 10V, I_D = | | R _{DS(ON)} | | | 0.21 | Ω |
| | 10A, T _C = 125°C | | | | 0.40 | |
| GATE THRESHOLD VOLTAGE V _{DS} = | = V _{GS} , I _D = 250μA | V _{GS(th)} | 2.0 | - | 4.0 | Volts |
| FORWARD TRANSCONDUCTANCE | | g _{fs} | 6.0 | - | - | S(1/Ω) |
| | $I_{\rm DS(on)}, I_{\rm D} = 10A$ | | | | | |
| ZERO GATE VOLTAGE DRAIN CURRE | | | - | | | |
| V_{DS} = 0.8xMax. Rating, V_{GS} = | | I _{DSS} | | 0.1 | 0.25 | mA |
| V _{DS} = 0.8xMax. Rating, V _{GS} = | = 0V, T _C = 125°C | | | 0.2 | 1.0 | |
| GATE TO SOURCE LEAKAGE FORWA | | I _{GSS} | - | - | 100 | nA |
| GATE TO SOURCE LEAKAGE REVERS | | | | | -100 | |
| TURN ON DELAY TIME | $V_{DD} = 100V,$ | t _{d(ON)} | - | 17 | - | |
| RISE TIME | I _D =14A, | t _r | | 52 | | nsec |
| TURN OFF DELAY TIME | $R_G = 5.0\Omega$, | t _{d(OFF)} | | 36 | | |
| FALL TIME | V _{GS} = 10V | t _f | | 30 | | |
| DIODE FORWARD VOLTAGE T _c = | = 25°C, I _S = -14A, | V _{SD} | - | - | -1.5 | Volts |
| | $V_{GS} = 0V$ | 4 | | | | |
| REVERSE RECOVERY TIME | T _J = 150°C, | t _{rr} | - | 350 | - | 2000 |
| | $ _{f} = _{S},$ | | | 350 | | nsec |
| | $\frac{100 \text{ /} \mu \text{sec}}{100 \text{ /} \mu \text{sec}}$ | - | | 4000 | | |
| | $V_{GS} = 0 V$ | Ciss | - | 1300 | - | ~ F |
| | $V_{DS} = 25 V$ | Coss | | 400 | | pF |
| REVERSE TRANSFER CAPACITANCE | f = 1.0MHz | C _{rss} | | 130 | | |



SENSITRON DATA SHEET 171 REVISION B



MECHANICAL DIMENSIONS: in Inches / mm

<u>TO-257</u>

PINOUT TABLE

| DEVICE TYPE | PIN 1 | PIN 2 | PIN 3 |
|-------------|-------|--------|--------|
| SHD226403 | DRAIN | SOURCE | GATE |
| SHD226403R | GATE | DRAIN | SOURCE |

DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.